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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/666,694	09/18/2003	Ofer Sneh	4551P002D2	1409
8791	7590 06/29/2004		EXAMINER	
22.11.22.1	SOKOLOFF TAYLOR &	COLEMAN, WILLIAM D		
	12400 WILSHIRE BOULEVARD, SEVENTH FLOOR LOS ANGELES, CA 90025		ART UNIT	PAPER NUMBER
200111102220, 011 90020			2823	
			DATE MAILED: 06/29/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)			
	10/666,694	SNEH ET AL.			
Office Action Summary	Examin r	Art Unit			
	W. David Coleman	2823			
The MAILING DATE of this communication apperiod for Reply	p ars on the cover sheet with the c	orrespond nce address			
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a rep - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may a reply be timely within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from e, cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).			
Status					
1)⊠ Responsive to communication(s) filed on 18 S	September 2003.				
	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.				
Disposition of Claims					
4) ☐ Claim(s) 73-75 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. 5) ☐ Claim(s) 74 and 75 is/are allowed. 6) ☐ Claim(s) 73 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or election requirement.					
Application Papers					
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) acc Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the E	cepted or b) objected to by the drawing(s) be held in abeyance. Section is required if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).			
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Bureat * See the attached detailed Office action for a list	nts have been received. Its have been received in Applicationity documents have been received in Application (PCT Rule 17.2(a)).	ion No ed in this National Stage			
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08 Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:				

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DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claim 73 is rejected under 35 U.S.C. 102(e) as being anticipated by Gates et al., U.S. Patent 6,203,613 B1.

Gates discloses a semiconductor device as claimed. See FIGS. 1A & 1B where Gates discloses the claimed limitations.

Pertaining to claim 73, Gates teaches a structure formed on a substrate comprising: a material layer 14 formed on the substrate 18 in which the material layer is pretreated by introducing a radical specie including any combination of O₂, H₂, H₂O, NH₃, NF₃, N₂, C1 and F to increase AHx (column 4, lines 40-65) termination sites on the surface of the material layer, where x is an integer and A is a non-metal capable of bonding with hydrogen H (see Example 6, where NH₃ is incorporated into the invention, column 10, lines 60-62); a film layer formed above said material layer by repeated introduction of a first precursor followed by a second precursor to deposit said film layer by atomic layer deposition, the first precursor to deposit a first reactive specie on the surface of the material layer, the surface when pretreated being more receptive to have additional bonding with the first reactive specie, due to the increase of AHx termination sites on the surface and the second precursor to deposit a second

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reactive specie to react with the deposited first reactive specie to form said film layer (see Example 5).

Allowable Subject Matter

Claims 74 and 75 allowed.

The following is an examiner's statement of reasons for allowance: the prior art does not anticipate nor render obviousness as to the further limitation of depositing an insulator layer as claimed on the ALD deposited insulating layer.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to W. David Coleman whose telephone number is 571-272-1856. The examiner can normally be reached on 9:00 AM-5:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 571-272-1855. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

W. David Coleman Primary Examiner Art Unit 2823

WDC